

NTLUD4C26N

Power MOSFET

30 V, 7.3 A, Dual N-Channel,
2.0x2.0x0.55 mm μ Cool™ UDFN6 Package

Features

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 2.0 x 2.0 x 0.55 mm for Board Space Saving
- Ultra Low $R_{DS(on)}$
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Power Load Switch
- Wireless Charging
- DC-DC Converters

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage			V_{GS}	± 12	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	7.3	A
		$T_A = 85^{\circ}\text{C}$		5.3	
	$t \leq 5\text{ s}$	$T_A = 25^{\circ}\text{C}$		9.1	
Power Dissipation (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	1.70	W
	$t \leq 5\text{ s}$	$T_A = 25^{\circ}\text{C}$		2.63	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	4.8	A
		$T_A = 85^{\circ}\text{C}$		3.4	
Power Dissipation (Note 2)		$T_A = 25^{\circ}\text{C}$	P_D	0.72	W
Pulsed Drain Current		$t_p = 10\text{ }\mu\text{s}$	I_{DM}	22	A
MOSFET Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode) (Note 1)			I_S	3.0	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size, 2 oz. Cu.

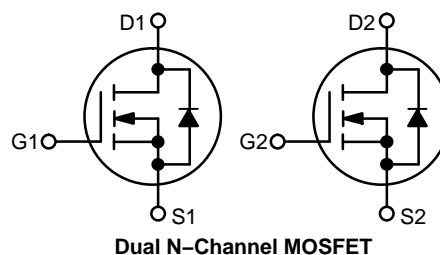


ON Semiconductor®

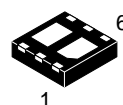
www.onsemi.com

MOSFET

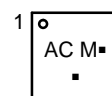
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	21 m Ω @ 10 V	7.3 A
	24 m Ω @ 4.5 V	
	26 m Ω @ 3.7 V	
	28 m Ω @ 3.3 V	
	36 m Ω @ 2.5 V	
	65 m Ω @ 1.8 V	



MARKING DIAGRAM

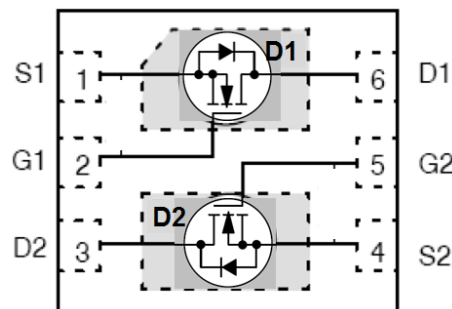


UDFN6
CASE 517BF
 μ COOL™



AC = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

NTLUD4C26N

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	73.6	°C/W
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	47.6	
Junction-to-Ambient – Steady State min Pad (Note 4)	$R_{\theta JA}$	174.4	

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

4. Surface-mounted on FR4 board using the minimum recommended pad size, 2 oz. Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
-----------	--------	----------------	-----	-----	-----	-------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 250$ μ A	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250$ μ A, ref to 25°C		7		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0$ V, $V_{DS} = 24$ V	$T_J = 25^\circ\text{C}$		1	μ A
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 12$ V			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250$ μ A	0.6		1.1	V
Negative Threshold Temp. Coefficient	$V_{GS(TH)}/T_J$			2.8		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 6.0$ A		17.5	21	m Ω
		$V_{GS} = 4.5$ V, $I_D = 5.0$ A		20	24	
		$V_{GS} = 3.7$ V, $I_D = 3.0$ A		21	26	
		$V_{GS} = 3.3$ V, $I_D = 3.0$ A		22	28	
		$V_{GS} = 2.5$ V, $I_D = 2.0$ A		25	36	
		$V_{GS} = 1.8$ V, $I_D = 1.0$ A		40	65	
Forward Transconductance	g_{FS}	$V_{DS} = 1.5$ V, $I_D = 5.0$ A		23		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0$ V, $f = 1$ MHz, $V_{DS} = 15$ V		460		pF
Output Capacitance	C_{OSS}			225		
Reverse Transfer Capacitance	C_{RSS}			27		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5$ V, $V_{DS} = 10$ V; $I_D = 5.0$ A		5.0	8.0	nC
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5$ V, $V_{DS} = 15$ V; $I_D = 5.0$ A		5.5	9.0	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.55		
Gate-to-Source Charge	Q_{GS}			2.5		
Gate-to-Drain Charge	Q_{GD}			1.1		

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5$ V (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5$ V, $V_{DD} = 15$ V, $I_D = 5.0$ A, $R_G = 1$ Ω		5		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(OFF)}$			13		
Fall Time	t_f			1.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width ≤ 300 μ s, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

NTLUD4C26N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
-----------	--------	----------------	-----	-----	-----	-------

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 2.0\text{ A}$	$T_J = 25^\circ\text{C}$		0.7	1.0	V
			$T_J = 125^\circ\text{C}$		0.6		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 2.0\text{ A}$			18.5		ns
Charge Time	t_a				9.3		
Discharge Time	t_b				9.1		
Reverse Recovery Charge	Q_{RR}				7.8		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

DEVICE ORDERING INFORMATION

Device	Package	Shipping [†]
NTLUD4C26NTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUD4C26NTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

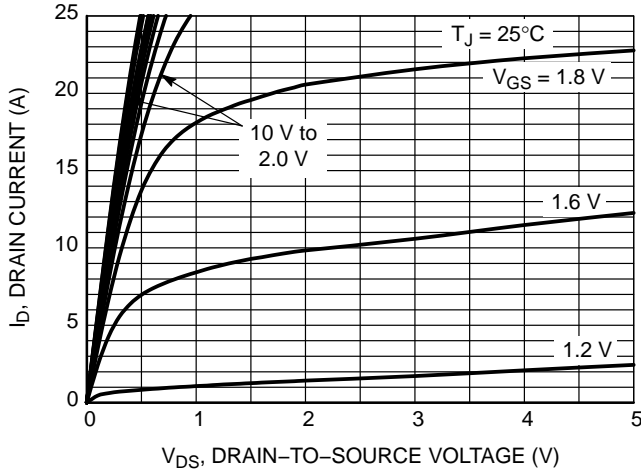


Figure 1. On-Region Characteristics

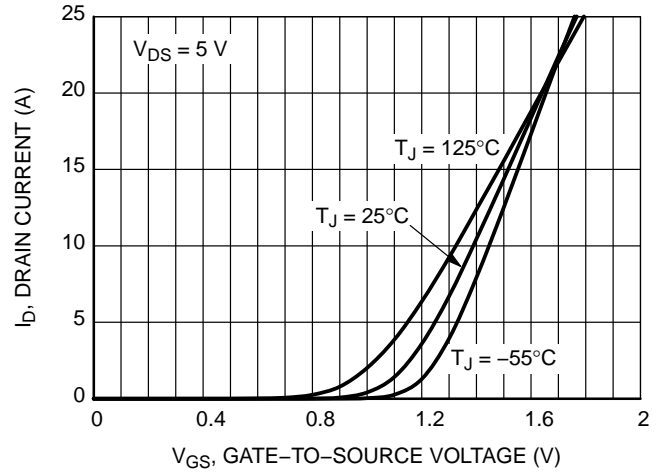


Figure 2. Transfer Characteristics

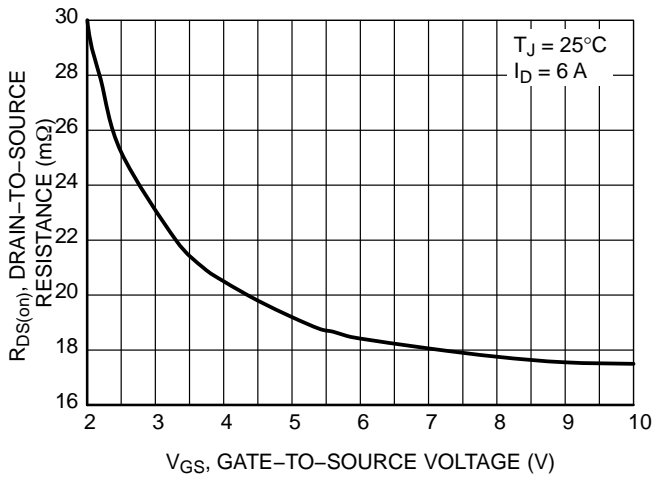


Figure 3. On-Resistance vs. Gate-to-Source Voltage

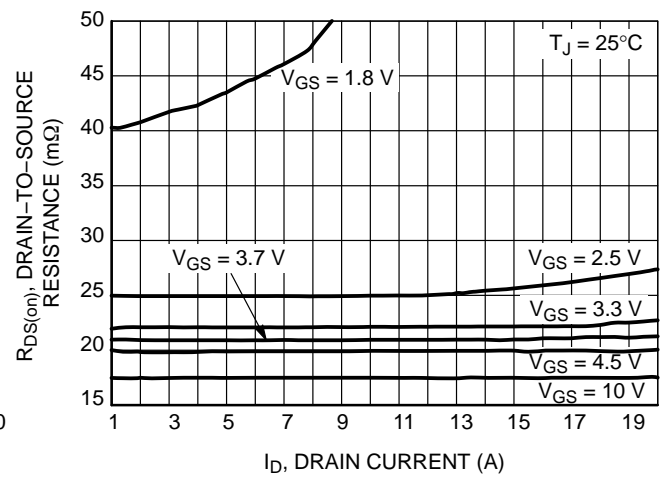


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

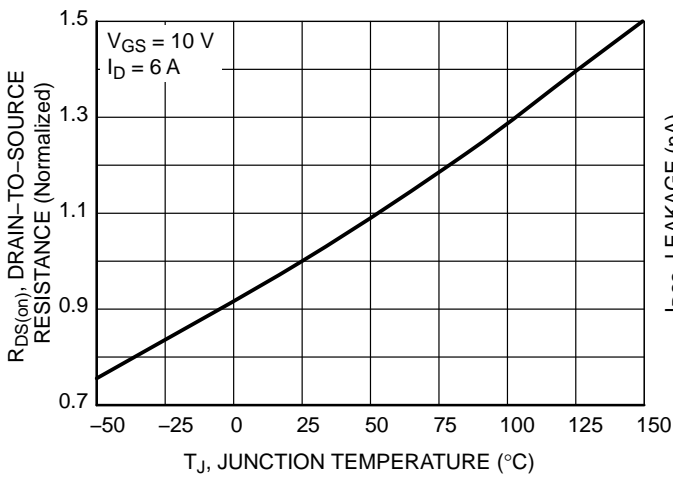


Figure 5. On-Resistance Variation with Temperature

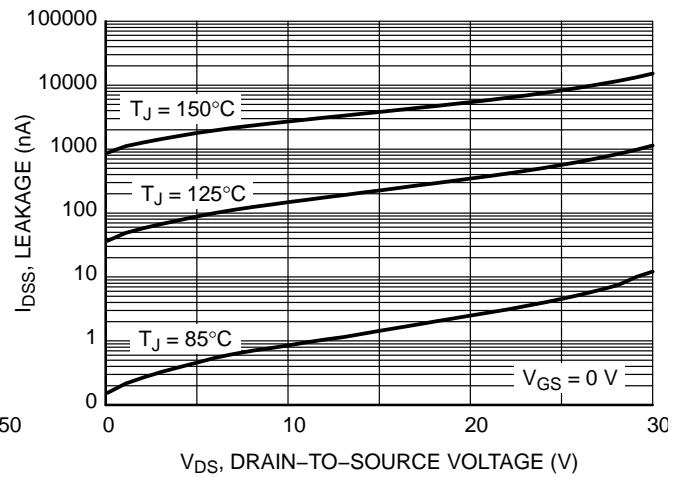


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

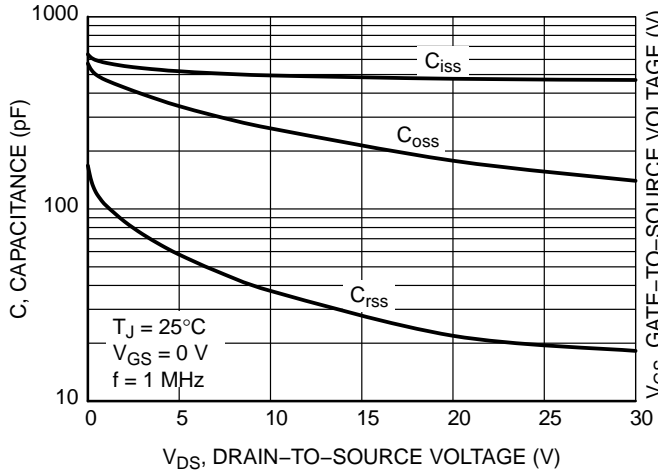


Figure 7. Capacitance Variation

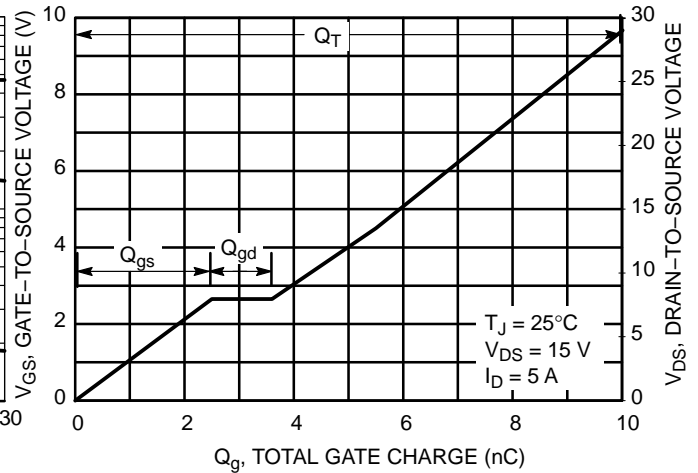


Figure 8. Gate-to-Source vs. Total Charge

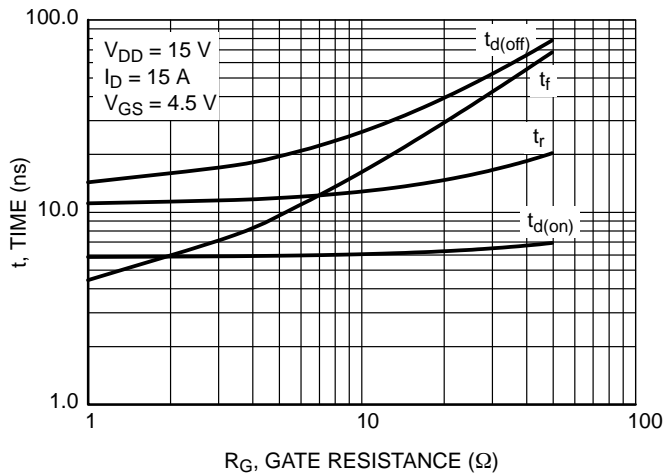


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

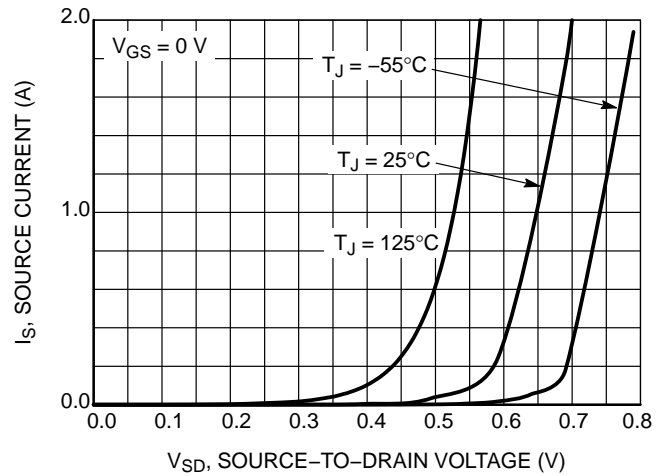


Figure 10. Diode Forward Voltage vs. Current

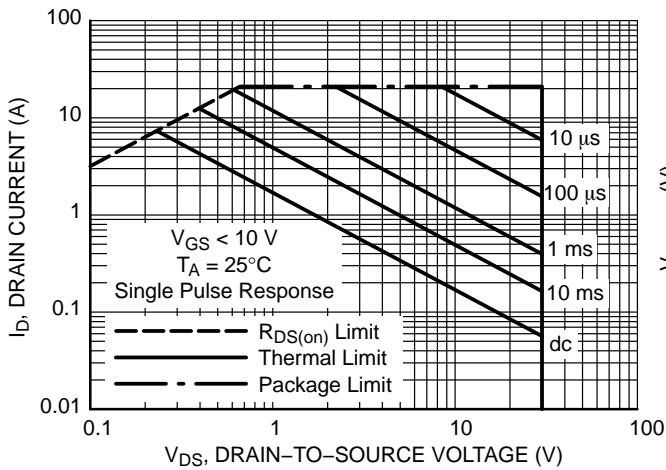


Figure 11. Maximum Rated Forward Biased Safe Operating Area

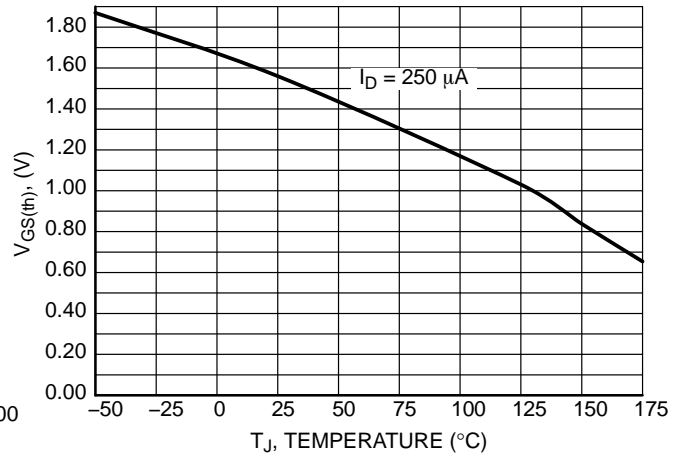


Figure 12. Threshold Voltage

NTLUD4C26N

TYPICAL CHARACTERISTICS

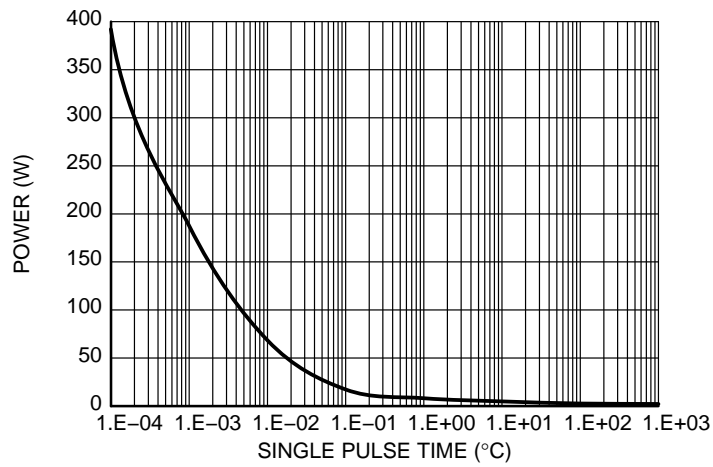


Figure 13. Single Pulse Maximum Power Dissipation

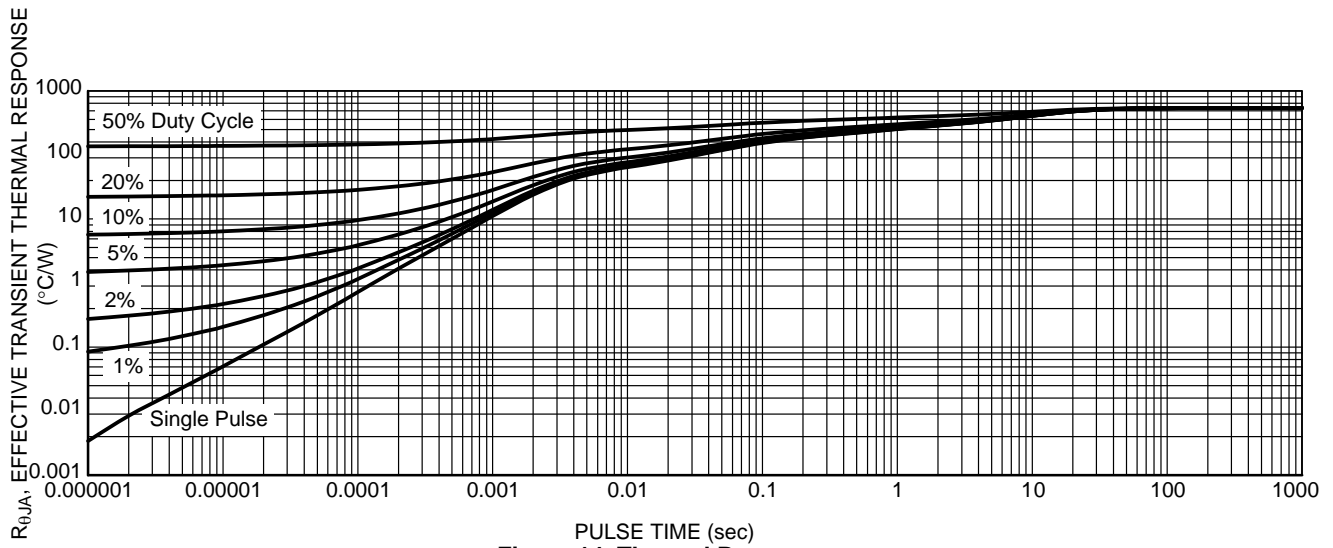


Figure 14. Thermal Response

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[ON Semiconductor:](#)

[NTLUD4C26NTAG](#)